

## PCN# 20230711003.1A Qualification of RFAB as an additional Fab site option for select HPA07 devices Change Notification / Sample Request

Date:August 09, 2023To:TOKYO ELECTRON DEVICE (DSTR) PCN

Dear Customer:

**Revision A** is to announce the <u>addition</u> of new devices that were not included in the original PCN notification.

This is an announcement of a change to a device that is currently offered by Texas Instruments. The details of this change are on the following pages.

Texas Instruments requires acknowledgement of receipt of this notification within **30** days of the date of this notice. Lack of acknowledgement of this notice within 30 days constitutes acceptance and approval of this change. If samples or additional data are required, requests must be received within **30 days** of this notification.

The changes discussed within this PCN will not take effect any earlier than the proposed first ship date on Page 3 of this notification, unless customer agreement has been reached on an earlier implementation of the change.

This notice does not change the end-of-life status of any product. Should product affected be on a previously issued product withdrawal/discontinuance notice, this notification does not extend the life of that product or change the life time buy offering/discontinuance plan.

For questions regarding this notice or to provide acknowledgement of this PCN, you may contact your local Field Sales Representative or the change management team.

For sample requests or sample related questions, contact your local Field Sales Representative.

Sincerely,

Change Management Team SC Business Services

## 20230711003.1<mark>A</mark> Attachment: 1

## **Products Affected:**

The devices listed on this page are a subset of the complete list of affected devices. According to our records, you have recently purchased these devices. The corresponding customer part number is also listed, if available.

## CUSTOMER PART NUMBER

DAC8811IBDGKR DAC8811IBDGKT DAC8811IBDRBT DAC8811ICDGKT DAC8801IDGKR DAC8801IDGKT DAC8811ICDRBT

DEVICE

null null null null null null

Technical details of this Product Change follow on the next page(s).

PCN Numb	er:		2023071	1003	3.1 <mark>A</mark>	PCN Date: August 09, 2023					
Title:	Qualific	ation of	RFAB a	s an a	additior	al Fab s	ite option	for se	elect HPAC	)7 devices	
Customer C	Contact	: Ch	ange Ma	anage	ement t	eam	Dept:	_	ality Servio	ces	
Proposed 1	. <sup>st</sup> Ship	Date:	Oct					epted until: August 11, 2023*			
*Sample re	-	s receiv	ed afte	er Au	gust 1	1, 2023	will not	be su	pported.		
Change Typ					- ·						
Assemb		266		┼┝┽	Design Data S			$\left  \frac{1}{2} \right $		Imp Material Imp Process	
	□ Assembly Materials □ Part number change ☑ Wafer Fab Site										
□ Mechanical Specification □ Test Site ☑ Wafer Fab Material											
Packing,	Packing/Shipping/Labeling       Image: Test Process       Image: Wafer Fab Process										
					-						
Description	of Ch				PCN	Deta	IS				
Description Revision A			the add	lition	of nine	new de	vices that	were	not inclue	ded in the original	
										roduct affected	
										<mark>: date for the new</mark>	
										accepted until 30	
the original			notice. I	ne p	roposec	1 <sup>35</sup> Ship	date of C	octobe	er 11, 202	<mark>3 still applies for</mark>	
the originar											
										l Wafer Fab site	
option for th	ne produ	icts liste	ed in the	e "Pro	duct Af	fected"	section of	this d	locument.		
	Current Fab Site New Fab Site										
Current F	ab	Proces	55	Wa	afer	r New Fab			Process Wafe		
Site	45				neter		Site			Diameter	
DP1DM5	5	HPA 0	7	200	)mm	m RFAB			HPA07	300mm	
			the 0.	-   D-							
Qual details Reason for			i the Qu	ai Da	ta Sect	ion.					
Continuity o											
Anticipated	l impac	t on Fo	orm, Fit	, Fur	nction,	<b>Qua lity</b>	or Relia	bility	(positive	e / negative):	
None											
Changes to	nrodu	ct iden	tificatio	on re	sulting	from t	his PCN:				
changes to	produ	et laen	lineati		Juiting	,					
Fab Site I	nforma	tion:									
Chip Si	ite	Chip S	Site Ori	-	ode	-	Site Cour	-	6	hip Site City	
DP1DM			(20L)	-			Code (21L)				
	-		DM5 RFB				USA USA			Dallas Richardson	
	·						USA				
Sample proc	luct shi	pping la	bel (not	actu	al prod	uct labe	)				
		Ē	1000000		ANNO 1						
TEXAS	TS	G4		1.4	. k. (	1P) SN7	4LS07NSR				
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MSL 1 /235C	UNLIM	03/29/04		\$£.	()	·) (	(11) 752.				
LBL: 5A	(L)T0	· 1750			i	2P) REV: 201) CSO:	SHE (21L)	003331 CC0:US	A		
LUL: JA	(-)10	1150			C	2L) ASO:	MLA (23L)	ACO: M	rs )		
Toxas Instruments Incorporated TI Information Selective Disclosure DCN# 20220711002 14											

Product Affected:										
ADS1191IPBS	ADS1192IRSMT	ADS1292IRSMR	DAC8811IBDRBT							
ADS1191IPBSR	ADS1291IPBS	ADS1292IRSMT	DAC8811ICDGKR							
ADS1191IRSMR	ADS1291IPBSR	DAC8801IDGKR	DAC8811ICDGKT							
ADS1191IRSMT	ADS1291IRSMR	DAC8801IDGKT	DAC8811ICDRBT							
ADS1192IPBS	ADS1291IRSMT	DAC8801IDRBT								
ADS1192IPBSR	ADS1292IPBS	DAC8811IBDGKR								
ADS1192IRSMR	ADS1292IPBSR	DAC8811IBDGKT								

#### **Qualification Results**

#### Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Name	Condition	Duration	Qual Device: ADS1292IRSMR	QBS Process Reference: <u>CD3232A1YFFR</u>	QBS Process Reference: <u>CD3232A1YFFR</u>	QBS Process Reference: AMC7836IPAP	QBS Process Reference: INA231AIYFDR	QBS Process Reference: INA231BIYFDR
HAST	A2	Biased HAST	130C/85%RH	96 Hours	-	3/231/0	3/231/0	-	-	-
UHAST	A3	Unbiased HAST	130C/85%RH	96 Hours	-	3/231/0	3/231/0	-	-	-
тс	A4	Temperature Cycle	-55C/125C	700 Cycles	-	3/231/0	3/231/0	-	-	-
HTSL	A6	High Temperature Storage Life	170C	420 Hours	-	3/231/0	3/231/0	-	1/77/0	2/154/0
HTOL	B1	Life Test	140C	480 Hours	-	1/77/0	2/154/0	-	-	-
HTOL	B1	Life Test	150C	300 Hours	-	-	-	1/77/0	1/77/0	2/154/0
ELFR	B2	Early Life Failure Rate	125C	48 Hours	-	1/1000/0	2/2000/0	-	1/1000/0	2/2000/0
ESD	E2	ESD CDM	-	200 Volts	-	3/9/0	3/9/0	-	-	-
ESD	E2	ESD CDM	-	250 Volts	-	-	-	1/3/0	-	2/6/0

Туре	#	Test Name	Condition	Duration	Qual Device: <u>ADS1292IRSMR</u>	QBS Process Reference: <u>CD3232A1YFFR</u>	QBS Process Reference: <u>CD3232A1YFFR</u>	QBS Process Reference: AMC7836IPAP	QBS Process Reference: INA231AIYFDR	QBS Process Reference: INA231BIYFDR
ESD	E2	ESD CDM	-	350 Volts	-	-	-	-	1/3/0	-
ESD	E2	ESD CDM	-	500 Volts	1/3/0	-	-	-		-
ESD	E2	ESD HBM	-	1000 Volts	1/3/0	3/9/0	3/9/0	1/3/0	1/3/0	2/6/0
LU	E4	Latch-Up	Per JESD78	-	1/3/0	3/9/0	3/9/0	1/3/0	1/6/0	2/12/0
CHAR	E5	Electrical Characterization	Per Datasheet Parameters	-	1/30/0	1/30/0	1/30/0	1/30/0	1/30/0	2/60/0
FTY	E6	Final Test Yield	-	-	1/Pass	-	-	-	-	-

QBS: Qual By Similarity
Qual Device ADS1292IRSMR is qualified at MSL2 260C

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
 The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-CHG-2208-068

## PCN Rev A Qual Memo

#### **Qualification Results**

#### Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Name	Condition	Duration	Qual Device: <u>DAC8811ICDGKT</u>	QBS Process Reference: <u>CD3232A1YFFR</u> (RFAB/JCAP)	QBS Process Reference: <u>CD3232A1YFFR</u> ( <u>RFAB/Clark</u> )	QBS Process Reference: INA231AIYFDR	QBS Process Reference: INA231BIYFDR	QBS Process Reference: DRV401AIRGWR
HAST	A2	Biased HAST	130C/85%RH	96 Hours	-	3/231/0	3/231/0	-	-	-
UHAST	A3	Unbiased HAST	130C/85%RH	96 Hours	-	3/231/0	3/231/0	-	-	-
тс	A4	Temperature Cycle	-55C/125C	700 Cycles	-	3/231/0	3/231/0	-	-	-
HTSL	A6	High Temperature Storage Life	170C	420 Hours	-	3/231/0	3/231/0	1/77/0	2/154/0	-
HTOL	В1	Life Test	140C	480 Hours	-	1/77/0	2/154/0	-	-	-
HTOL	В1	Life Test	150C	300 Hours	-	-	-	1/77/0	2/154/0	2/154/0
ELFR	B2	Early Life Failure Rate	125C	48 Hours	-	1/1000/0	2/2000/0	1/1000/0	2/2000/0	-
ESD	E2	ESD CDM	-	200 Volts	-	-	3/9/0	-	-	-
ESD	E2	ESD CDM	-	1000 Volts	1/3/0	-	-	-	2/6/0	2/6/0

Туре	#	Test Name	Condition	Duration	Qual Device: DAC8811ICDGKT	QBS Process Reference: CD3232A1YFFR (RFAB/JCAP)	QBS Process Reference: <u>CD3232A1YFFR</u> ( <u>RFAB/Clark)</u>	QBS Process Reference: INA231AIYFDR	QBS Process Reference: INA231BIYFDR	QBS Process Reference: <u>DRV401AIRGWR</u>
ESD	E2	ESD CDM	-	225 Volts	-	3/9/0	3/9/0	-	-	-
ESD	E2	ESD CDM	-	350 Volts	-	-	1/3/0	2/6/0	-	-
ESD	E2	ESD HBM	-	4000 Volts	1/3/0	-	-	-	-	-
ESD	E2	ESD HBM	-	1500 Volts	-	3/9/0	1/3/0	1/3/0	2/6/0	-
ESD	E2	ESD HBM		1000 Volts	-	-	-	-	-	2/6/0
LU	E4	Latch-Up	Per JESD78	-	-	3/9/0	3/9/0	1/6/0	2/12/0	2/12/0
CHAR	E5	Electrical Characterization	Per Datasheet Parameters	-	1/30/0	1/30/0	1/30/0	1/30/0	2/60/0	1/30/0
FTY	E6	Final Test Yield	-	-	1/Pass	-	-	-	-	-

QBS: Qual By Similarity

Qual Device DAC8811ICDGKT is qualified at MSL2 260C

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-CHG-2207-042

For questions regarding this notice, e-mails can be sent to Change Management team or your local Field Sales Representative.

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